

2811



8013-1139

PATENTS

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of

Atsushi YAMAGUCHI et al.

Confirmation No. 1202

Serial No. 09/944,186

Group 2811

Filed September 4, 2001

Examiner Shouxiang Hu

NITRIDE BASED SEMICONDUCTOR  
LIGHT-EMITTING DEVICE

RECEIVED  
JUL 30 2003  
12 2800 MAIL ROOM

REPLACEMENT OF REFERENCES OF IDS OF January 3, 2002

Commissioner for Patents

Alexandria, VA 22313-1450

Sir:

A call from the Examiner who has charge of this application advised us that the references cited in the Information Disclosure Statement of January 3, 2002 are missing from the PTO file.

These are replaced herewith. Also attached is a copy of the IDS of that date and the postcard receipt proving its filing.

Respectfully submitted,

YOUNG & THOMPSON

By

Robert J. Patch  
Attorney for Applicants  
Registration No. 17,355  
745 South 23rd Street  
Arlington, VA 22202  
Telephone: 703/521-2297

June 26, 2003  
RJP/bsg



1/3/02

THE STAMP OF THE PATENT OFFICE MAIL HEREON  
ACKNOWLEDGES THE RECEIPT OF THE BELOW-IDENTIFIED  
DOCUMENT ON THE DATE INDICATED BY SUCH STAMP.

In re: Atsushi YAMAGUCHI et al.  
S.N. 09/944,186 Group 2811

INFORMATION DISCLOSURE STATEMENT WITH PTO FORM  
1449 WITH 10 REFERENCES.

RJP/cam



TO 2809 MAIL ROOM

JUN 30 2003

RECEIVED



PATENTS

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of

Atsushi YAMAGUCHI et al.

Serial No. 09/944,186

GROUP 2811

Filed September 4, 2001

Examiner Unassigned

NITRIDE BASED SEMICONDUCTOR LIGHT-EMITTING DEVICE

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents

Washington, D.C. 20231

Sir:

In compliance with Rules 1.97 and 1.98, and full-  
fillment of the duty of disclosure under Rule 1.56, the accom-  
panying documents, copies of which are attached to this state-  
ment, are made of record on the enclosed sheet.

A concise explanation of the relevance of these  
items is that these references were discovered during any  
searches they or their client had made, or that they were con-  
sidered in the preparation of the application.

Respectfully submitted,

YOUNG & THOMPSON

By

Robert J. Patch  
Attorney for Applicants  
Registration No. 17,355  
745 South 23rd Street  
Arlington, VA 22202  
Telephone: 703/521-2297

January 3, 2002

RECEIVED  
JUN 30 2004  
10 2800 MAIL ROOM

FORM PTO-1449

U.S. DEPARTMENT OF COMMERCE  
PATENT AND TRADEMARK OFFICEATTY. DOCKET NO.  
PF-2871SERIAL NO.  
09/944,186INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT

(Use several sheets if necessary)

JUN 26 2003

37 CFR 1.98(b)

APPLICANT

Atsushi YAMAGUCHI et al.

FILING DATE

September 4, 2001

GROUP

2811

## U.S. PATENT DOCUMENTS

EXAMINER INITIAL		PATENT NUMBER	ISSUE DATE	PATENTEE	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	AA						

## FOREIGN PATENT OR PUBLISHED FOREIGN PATENT APPLICATION

		DOCUMENT NO.	PUBL. DATE	COUNTRY OR PATENT OFFICE	CLASS	SUB CLASS	TRANSLATION YES NO
	AI	A 11-307866	11/99	JP			with English abstract
	AJ	A 11-340580	12/99	JP			with English abstract
	AK						

## OTHER DOCUMENTS (Including Author, Title, Date, Relevant Pages, Place of Publication)

AL	Shuji NAKAMURA, "Current Status and Future Prospects of InGaN-Based Laser Diodes," JSAP International, Jan. 2000, Tokushima, Japan, pp. 5-17.
AM	Masaru KURAMOTO et al., "Towards a Durable InGaN MQW LD--Room Temperature CW Operation of InGaN MQW Laser," NEC Res. & Develop., V. 41, January 2000, pp. 74-86.
AN	Shuji NAKAMURA et al., "InGaN/GaN/AlGaN-Based Laser Diodes with Modulation-Doped Strained-Layer Superlattices," Jpn. J. Appl. Phys., V. 36, 1997, pp. L1568-L1571.
AO	Akira USUI et al., "Thick GaN Epitaxial Growth with Low Dislocation Density by Hydride Vapor Phase Epitaxy," Jpn. J. Appl. Phys., V. 36, 1997, pp. L899-L902.
AP	Shigefusa CHICHIBU, "Spatially Resolved Cathodoluminescence Spectra of InGaN Quantum Wells," Appl. Phys. Lett. 71, 1997, pp. 2346-2348.
AQ	W. W. CHOW et al., "Microscopic Theory of Gain for an InGaN/AlGaN Quantum Well Laser," Appl. Phys. Lett. 71, 1997, pp. 2608-2610.
AR	A. Atsushi YAMAGUCHI et al., "Optical Recombination Processes in High-Quality GaN Films and InGaN Quantum Wells Grown on Facet-Initiated Epitaxial Lateral Overgrown GaN Substrates," Jpn. J. Appl. Phys., V. 39, 2000, pp. 2402-2406.
AS	G. Martin et al., "Valence-Band Discontinuities of Wurtzite GaN, AlN, and InN Heterojunctions Measured by X-Ray Photoemission Spectroscopy," Appl. Phys. Lett. 68, 1996, pp. 2541-2543.
AT	

EXAMINER

DATE CONSIDERED

EXAMINER: Initial citation considered. Draw line through citation if not in conformance and not considered.  
Include copy of this form with next communication to applicant.